R^3, R^4 and R^5 are each independently hydrogen or optionally substituted alkyl;

[m and n are each independently] n is 0 to 4; and

x, y and z are each greater than 0 and are mole percent of the respective units of the polymer.

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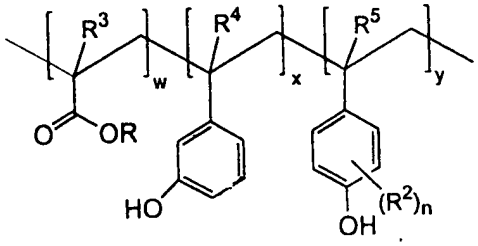
6. (amended) The photoresist of claim 1 wherein the polymer comprises a structure of Formula II:



II

wherein R is optionally substituted alkyl;

[R^1 and] each R^2 is [are each] the same or different non-hydrogen substituent [substituents];

R^3, R^4 and R^5 are each independently hydrogen or optionally substituted alkyl;

[m and n are each independently] n is 0 to 4; and

w, x and y are each greater than 0 and are the mole percents of the respective polymer units.

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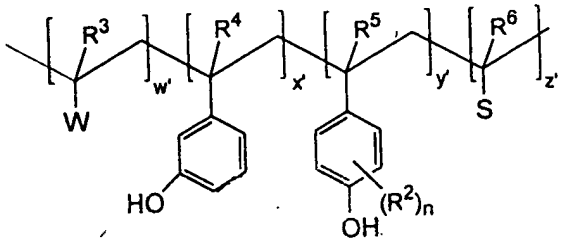
8. (amended) The photoresist of claim 1 wherein the polymer comprises a structure of Formula III:



III

wherein W comprises an acid-labile group;

[R^1 and] each R^2 is [are each] the same or different non-hydrogen substituents;

R^3, R^4, R^5 and R^6 are each independently hydrogen or optionally substituted alkyl;

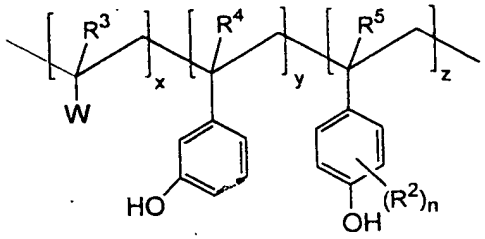
m and n are each independently 0 to 4; and

S is a group that does not contain acidic or reactive moieties;

w', x', y' and z' are each greater than 0 and are mole fractions of the respective polymer units.

17. (amended) A polymer that comprises 1) acid labile groups; 2) meta-hydroxyphenyl groups[,]; and 3) a para-hydroxyphenyl group, wherein the meta-hydroxyphenyl groups each has a single meta-hydroxy moiety and is unsubstituted at other available ring positions.

18. A polymer of claim 17 wherein the polymer comprises a structure of Formula I:



I

wherein W comprises an acid-labile group;

[R^1 and] each R^2 [are each] is the same or different non-hydrogen substituent;

R^3, R^4 and R^5 are each independently hydrogen or optionally substituted alkyl;

[m and n are each independently] n is 0 to 4; and

x, y and z are each greater than 0 and are mole percent of the respective units of the polymer.

Please add the following new claims.

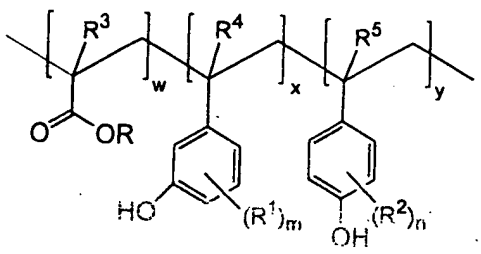
21. A photoresist of claim 6 wherein R is tert-butyl, adamantyl, tetrahydropyranal or norbornyl.

22. A polymer of claim 20 wherein R is tert-butyl, adamantyl, tetrahydropyranal or norbornyl.

23. A polymer of claim 20 wherein the sum of w, x, y and z is at least about 90 mole percent of total units of the polymer.

24. A photoresist composition comprising a photoactive component and a resin that comprises a polymer that comprises 1) an acrylate acid labile group; 2) a meta-hydroxyphenyl group; and 3) a para-hydroxyphenyl group.

25. The photoresist of claim 24 wherein the polymer is represented by the following Formula II:



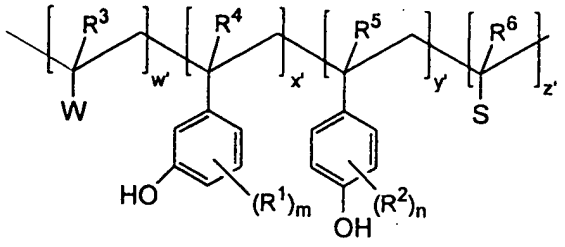
II

wherein R is optionally substituted alkyl;
R^1 and R^2 are each the same or different non-hydrogen substituents;
R^3, R^4 and R^5 are each independently hydrogen or optionally substituted alkyl;
m and n are each independently 0 to 4; and
w, x and y are each greater than 0 and are mole percents of the respective polymer units.

26. A photoresist of claim 25 wherein R is tert-butyl, adamantyl, tetrahydropyranal or norbornyl.

27. The photoresist of claim 25 wherein the sum of w, x and y is at least about 90 percent.

28. The photoresist of claim 24 wherein the polymer is represented by the following Formula III:



III

wherein W comprises an acid-labile group;

R^1 and R^2 are each the same or different non-hydrogen substituents;

R^3, R^4, R^5 and R^6 are each independently hydrogen or optionally substituted alkyl;

m and n are each independently 0 to 4; and

S is a group that does not contain acidic or reactive moieties;

w', x', y' and z' are each greater than 0 and are mole percents of the respective polymer units.

29. A photoresist of claim 28 wherein the sum of w', x', y' and z' is at least about 90 percent.

30. A method for forming a photoresist relief image, comprising:

a) applying a layer of a photoresist composition of claim 24 on a substrate; and

b) exposing and developing the photoresist layer on the substrate to yield a photoresist relief image.

31. The method of claim 30 wherein the substrate is a microelectronic wafer of a flat panel display substrate.

32. An article of manufacture comprising a substrate having coated thereon a photoresist composition of claim 24.